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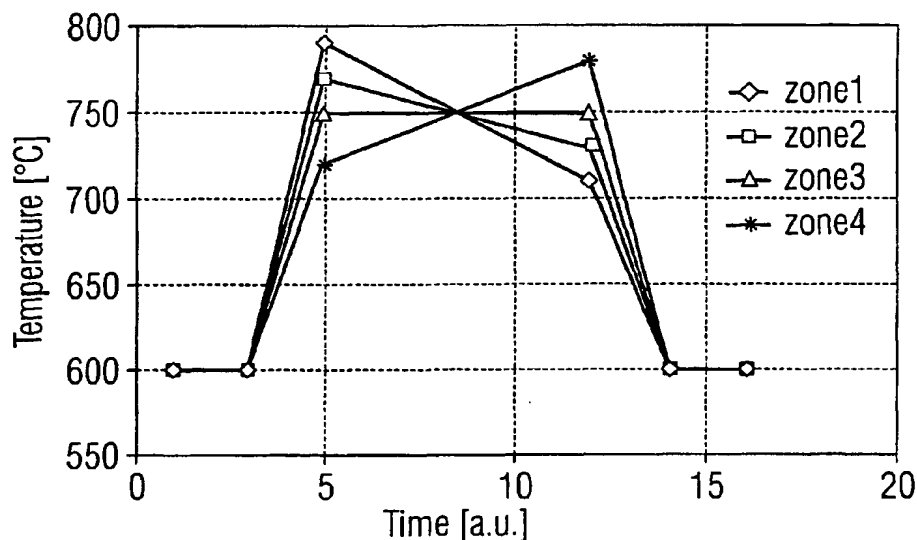
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(54) Title: HEATING SYSTEM AND METHOD FOR HEATING AN ATMOSPHERIC REACTOR



(57) Abstract: The present invention provides a heating system for heating a deposition/oxidation reactor in which a plurality of wafers is held perpendicularly to the reactant gas flowing direction which is parallel to the longitudinal axis of the reactor, so as to enable a deposition or oxidation reaction. The heating system is adapted to change the reactor temperature during the process. Further, the invention provides a method for heating a reactor in which a plurality of wafers is held perpendicularly to the reactant gas flowing direction, so as to enable a reaction, wherein the reactor temperature is changed during the process. Preferably, each of a plurality of reactor zones, into which the reactor is divided in a direction parallel to the reactant gas flowing direction, is heated at a different temperature profile.



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